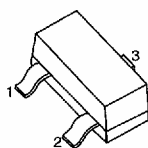


DIODES



SOT-23/TO-236AB

'TMPD' GENERAL-PURPOSE and LOW-LEAKAGE DIODES
ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ\text{C}$

Device Type	Description	Marking	I_F Max. (mA)	V_{BR} Min. (V)	V_F		I_R Max. (nA)	t_{rr} Max. (ns)	C_O Max. (pF)	Pinning 1, 2, 3
					Max. (V)	@ I_F (mA)				
TMPD914	General-Purpose	5D	600	100	1.0	10	25	4.0	6.0	A NC K
TMPD2836	Common Anode	A2	500	75	1.0	10	0.10	6.0	4.0	K1 K2 A
TMPD2838	Common Cathode	A6	500	75	1.0	10	0.10	6.0	4.0	A1 A2 K
TMPD4148	General-Purpose	5D	600	100	1.0	10	25	4.0	4.0	A NC K
TMPD6050	Low Leakage	5A	600	70	1.1	100	0.10	10	2.5	A NC K
TMPD7000	Dual In-Series	5C	600	100	1.1	100	0.30	15	1.5	A1 K2 A/K

'TMPD' SCHOTTKY DIODES (see also A8920SLR)
ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ\text{C}$

Device Type	V_{BR} Min. (V)	V_F Max.		I_R Max.			C_O Max. (pF)	Pinning 1, 2, 3
		$I_F = 1$ mA (V)	$I_F = 10$ mA (mA)	$V_R = 1$ V (nA)	$V_R = 20$ V (nA)	$V_R = 50$ V (nA)		
TMPD5711	70	0.41	0.75	—	50	200	2.0	A NC K
TMPD6916	40	0.34	0.47	100	200	—	5.0	A NC K
TMPD6924	70	0.41	0.75	—	—	200	2.0	A NC K

PRO-ELECTRON DEVICE TYPES
ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ\text{C}$

Device Type	Description	Marking	I_F Max. (mA)	V_{BR} Min. (V)	V_F		I_R Max. (nA)	t_{rr} Max. (ns)	C_O Max. (pF)	Pinning 1, 2, 3
					Max. (V)	@ I_F (mA)				
BAS16	General-Purpose	A6	600	75	0.72	1.0	1000	6.0	2.0	A NC K
BAV70	Common Cathode	A4	100	70	0.86	10	5000	6.0	1.5	A1 A2 K
BAV99	Dual In-Series	A7	70	70	1.1	50	2500	6.0	2.0	A1 K2 A/K
BAW56	Common Anode	A1	70	70	1.1	50	2500	6.0	2.0	K1 K2 A